

## Description

The 2N7002KW uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

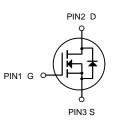
#### **General Features**

 $V_{DS} = 60V I_D = 0.115A$  $R_{DS(ON)} < 3\Omega @ V_{GS} = 10V$ 

# D



N-Channel MOSFET



## Application

Battery protection Load switch Uninterruptible power supply

#### Package Marking and Ordering Information

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Product ID	Pack	Marking	Qty(PCS)
2N7002KW	SOT-323		3000

## Absolute Maximum Ratings (T<sub>A</sub>=25<sup>°</sup>C unless otherwise noted)

Parameter	Limit	Unit
Drain-Source Voltage	60	V
Gate-Source Voltage	±20	V
Drain Current-Continuous	0.115	A
Maximum Power Dissipation	0.2	W
Operating Junction and Storage Temperature Range	-55 To 150	°C
Thermal Resistance, Junction-to-Ambient (Note 2)	625	°C/W
	Drain-Source Voltage         Gate-Source Voltage         Drain Current-Continuous         Maximum Power Dissipation         Operating Junction and Storage Temperature Range	Drain-Source Voltage       60         Gate-Source Voltage       ±20         Drain Current-Continuous       0.115         Maximum Power Dissipation       0.2         Operating Junction and Storage Temperature Range       -55 To 150



## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0 V, I <sub>D</sub> =250 μA	60			V
Gate-Threshold Voltage	V <sub>(GS)th</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250 \ \mu A$	1	1.6	2.5	v
Gate-body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =0 V, V <sub>GS</sub> =±20 V			±80	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60 V, V <sub>GS</sub> =0 V			80	nA
On-state Drain Current	I <sub>D(on)</sub>	V <sub>GS</sub> =10 V, V <sub>DS</sub> =7 V	500			mA
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10 V, I <sub>D</sub> =115mA		1.3	3	Ω
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =50mA		2	5	
Forward Trans conductance	<b>g</b> fs	V <sub>DS</sub> =10 V, I <sub>D</sub> =200mA	80			ms
Drain course on voltage	V <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =500mA			3.75	V
Drain-source on-voltage		V <sub>GS</sub> =5V, I <sub>D</sub> =50mA			0.375	V
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =115mA, V <sub>GS</sub> =0 V	0.55		1.2	V
Input Capacitance *	C <sub>iss</sub>				50	
Output Capacitance *	Coss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz			25	pF
Reverse Transfer Capacitance*	C <sub>rss</sub>				5	
SWITCHING TIME		·				

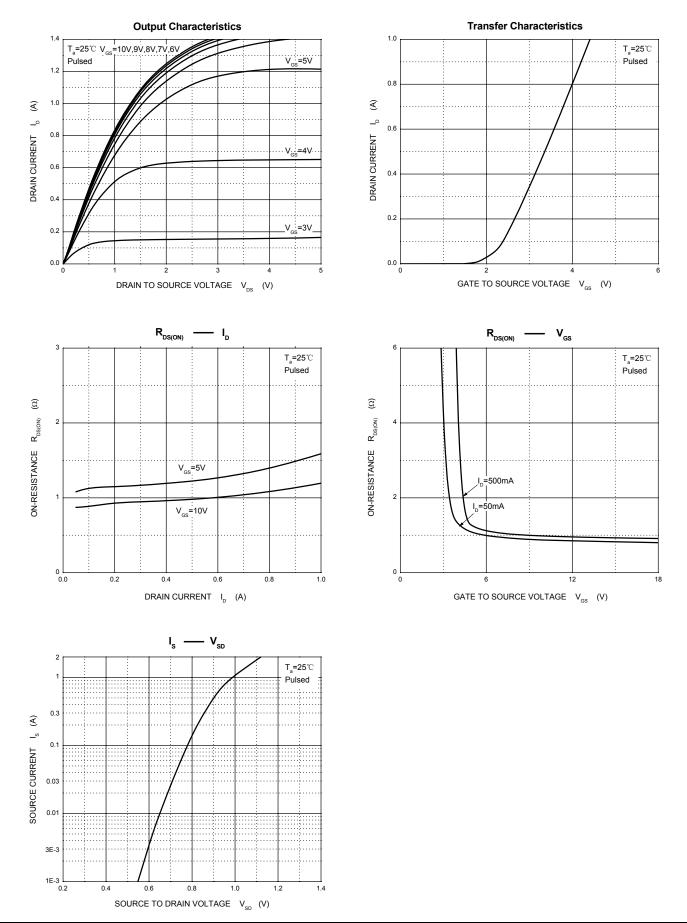
Turn-on Time*	t <sub>d(on)</sub>	$V_{DD}=25 \text{ V}, \text{ R}_{L}=50\Omega,$		20	20	
Turn-off Time*	$t_{\text{d(off)}}$	I <sub>D</sub> =500mA,V <sub>GEN</sub> =10 V R <sub>G</sub> =25Ω		40	ns	

\*These parameters have no way to verify.



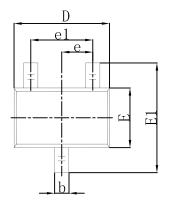
## 2N7002KW N-Channel Enhancement Mode MOSFET

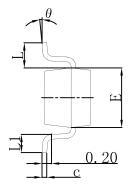
#### **Typical Characteristics**

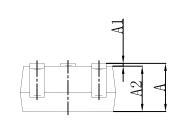




# SOT-323 Package Outline Dimensions







Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.200	0.400	0.008	0.016	
С	0.080	0.150	0.003	0.006	
D	2.000	2.200	0.079	0.087	
E	1.150	1.350	0.045	0.053	
E1	2.150	2.450	0.085	0.096	
е	0.650	) TYP	0.026	TYP	
e1	1.200	1.400	0.047	0.055	
L	0.525 REF		0.021 REF		
L1	0.260	0.460	0.010	0.018	
K	0°	8°	0°	8°	



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